



16-Mb (1024K x 16) Static RAM

Features

- **Very high speed: 55 ns and 70 ns**
- **Wide voltage range: 1.65V to 2.2V**
- **Ultra-low active power**
 - Typical active current: 1.5 mA @ f = 1 MHz
 - Typical active current: 18 mA @ f = f_{MAX}
- **Ultra-low standby power**
- **Easy memory expansion with \overline{CE}_1 , CE_2 , and \overline{OE} features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Packages offered in a 48-ball FBGA**

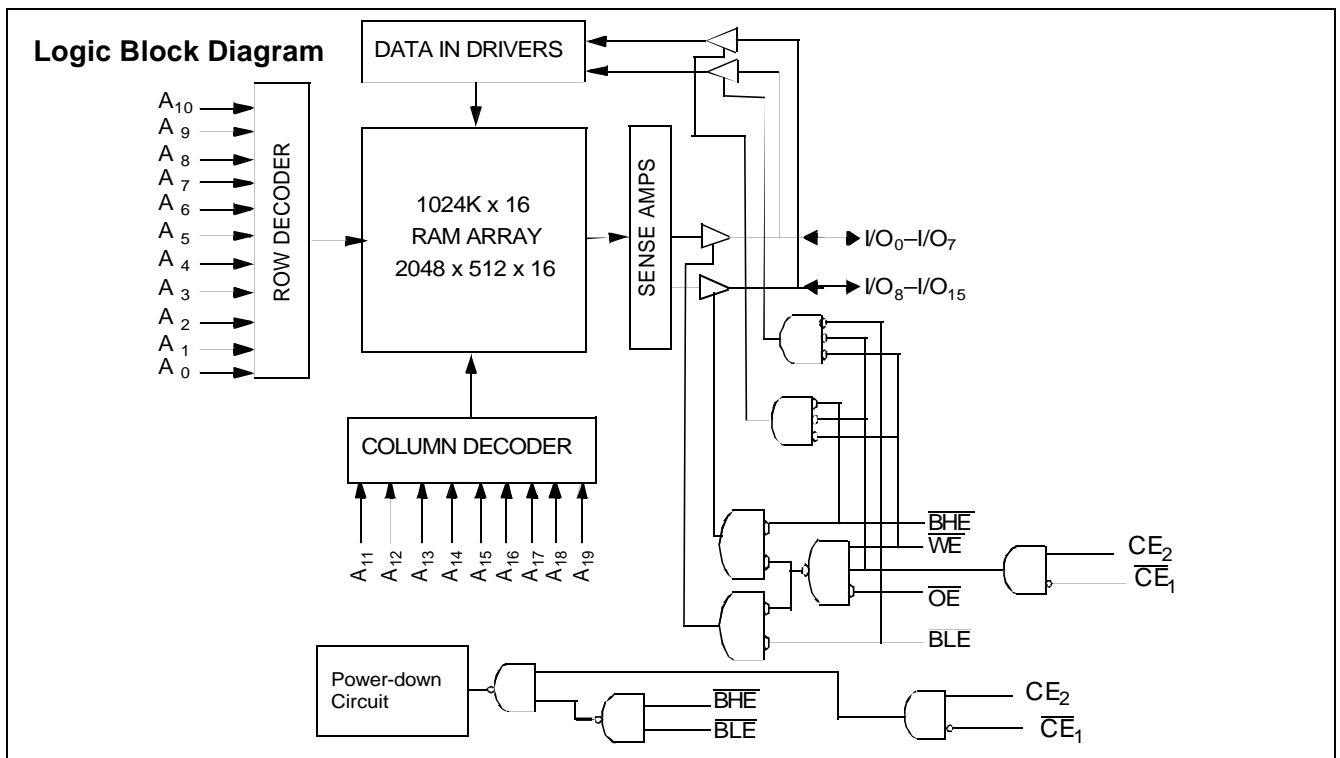
Functional Description^[1]

The CY62167DV20 is a high-performance CMOS static RAM organized as 1024K words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption by 99% when addresses are not

toggling. The device can be put into standby mode reducing power consumption by more than 99% when deselected Chip Enable 1 (\overline{CE}_1) HIGH or Chip Enable 2 (CE_2) LOW or both BHE and BLE are HIGH. The input/output pins (I/O₀ through I/O₁₅) are placed in a high-impedance state when: deselected Chip Enable 1 (\overline{CE}_1) HIGH or Chip Enable 2 (CE_2) LOW, outputs are disabled (\overline{OE} HIGH), both Byte High Enable and Byte Low Enable are disabled (\overline{BHE} , BLE HIGH) or during a write operation (Chip Enable 1 (\overline{CE}_1) LOW and Chip Enable 2 (CE_2) HIGH and WE LOW).

Writing to the device is accomplished by taking Chip Enable 1 (\overline{CE}_1) LOW and Chip Enable 2 (CE_2) HIGH and Write Enable (WE) input LOW. If Byte Low Enable (BLE) is LOW, then data pins (A₀ through A₁₉). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address.

Reading from the device is accomplished by taking Chip Enable 1 (\overline{CE}_1) LOW and Chip Enable 2 (CE_2) HIGH and Output Enable (\overline{OE}) LOW while forcing the Write Enable (\overline{WE}) HIGH. If Byte Low Enable (\overline{BLE}) is LOW, then data from memory will appear on I/O₈ to I/O₁₅. See the truth table at the back of this data sheet for a complete description of read and write modes.

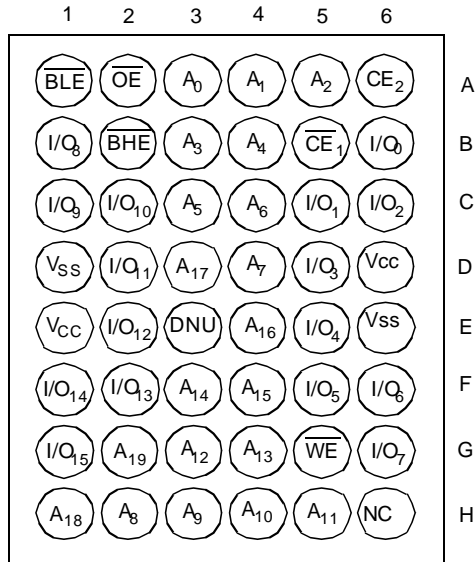


Note:

1. For best practice recommendations, please refer to the Cypress application note "System Design Guidelines" on <http://www.cypress.com>.



Pin Configuration^[2, 3.]



Notes:

2. DNU pins are to be connected to V_{SS} or left open.
3. NC pins are not connected on the die.



CY62167DV20 MoBL2™

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with

Power Applied..... -55°C to +125°C

Supply Voltage to Ground

Potential -0.2V to $V_{CCMAX} + 0.2V$

DC Voltage Applied to Outputs

in High-Z State^[4, 5]..... -0.2V to $V_{CCMAX} + 0.2V$

DC Input Voltage^[4, 5] -0.2V to $V_{CCMAX} + 0.2V$

Output Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage > 2001V
(per MIL-STD-883, Method 3015)

Latch-up Current..... > 200 mA

Operating Range

| Range | Ambient Temperature (T _A) | V _{CC} ^[6] |
|------------|---------------------------------------|--------------------------------|
| Industrial | -40°C to +85°C | 1.65V to 2.2V |

Product Portfolio

| Product | V _{CC} Range(V) | | | Speed (ns) | Power Dissipation | | | | | |
|---------------|--------------------------|------|------|------------|---------------------------------|------|----------------------|------|--------------------------------|------|
| | | | | | Operating, I _{CC} (mA) | | | | Standby, I _{SB2} (μA) | |
| | Min. | Typ. | Max. | | f = 1 MHz | | f = f _{MAX} | | | |
| | | | | | Typ. ^[7] | Max. | Typ. ^[7] | Max. | Typ. ^[7] | Max. |
| CY62167DV20L | 1.65 | 1.8 | 2.2 | 55 | 1.5 | 5 | 18 | 35 | 2.5 | 40 |
| | | | | 70 | | | 15 | 30 | | |
| CY62167DV20LL | 1.65 | 1.8 | 2.2 | 55 | 1.5 | 5 | 18 | 35 | 2.5 | 30 |
| | | | | 70 | | | 15 | 30 | | |

DC Electrical Characteristics (over the operating range)

| Parameter | Description | Test Conditions | CY62167DV20-55 | | | CY62167DV20-70 | | | Unit |
|------------------|---|---|----------------|---------------------|-----------------------|----------------|---------------------|-----------------------|------|
| | | | Min. | Typ. ^[7] | Max. | Min. | Typ. ^[7] | Max. | |
| V _{OH} | Output HIGH Voltage | I _{OH} = -0.1 mA, V _{CC} = 1.65V | 1.4 | | | 1.4 | | | V |
| V _{OL} | Output LOW Voltage | I _{OL} = 0.1 mA, V _{CC} = 1.65V | | | 0.2 | | | 0.2 | V |
| V _{IH} | Input HIGH Voltage | | 1.4 | | V _{CC} + 0.2 | 1.4 | | V _{CC} + 0.2 | V |
| V _{IL} | Input LOW Voltage | | -0.2 | | 0.4 | -0.2 | | 0.4 | V |
| I _{Ix} | Input Leakage Current | GND ≤ V _I ≤ V _{CC} | -1 | | +1 | -1 | | +1 | μA |
| I _{OZ} | Output Leakage Current | GND ≤ V _O ≤ V _{CC} , Output Disabled | -1 | | +1 | -1 | | +1 | μA |
| I _{CC} | V _{CC} Operating Supply Current | f = f _{MAX} = 1/t _{RC} , V _{CC} = 2.2V, I _{OUT} = 0mA, CMOS level | | 18 | 35 | | 15 | 30 | mA |
| | | f = 1 MHz | | 1.5 | 5 | | 1.5 | 5 | |
| I _{SB1} | Automatic CE Power-down Current – CMOS Inputs | CE ₁ ≥ V _{CC} - 0.2V, CE ₂ ≤ 0.2V, V _{IN} ≥ V _{CC} - 0.2V, V _{IN} ≤ 0.2V, f = f _{MAX} (Address and Data Only), f = 0 (OE, WE, BHE and BLE) | L | 2.5 | 40 | | 2.5 | 40 | μA |
| | | | LL | 2.5 | 30 | | 2.5 | 30 | |
| I _{SB2} | Automatic CE Power-down Current – CMOS Inputs | CE ₁ ≥ V _{CC} - 0.2V, CE ₂ ≤ 0.2V, V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V, f = 0, V _{CC} = 2.2V | L | 2.5 | 40 | | 2.5 | 40 | μA |
| | | | LL | 2.5 | 30 | | 2.5 | 30 | |

Capacitance^[8]

| Parameter | Description | Test Conditions | Max. | Unit |
|------------------|--------------------|--|------|------|
| C _{IN} | Input Capacitance | TA = 25°C, f = 1 MHz | 8 | pF |
| C _{OUT} | Output Capacitance | V _{CC} = V _{CC(typ)} | 10 | pF |

4. V_{IL(min)} = -2.0V for pulse durations less than 20 ns.

5. V_{IH(max)} = V_{CC} + 0.75V for pulse durations less than 20 ns.

6. Full device AC operation assumes a 100 μs ramp time from 0 to V_{CC(min)} and 100 μs wait time after V_{CC} stabilization.

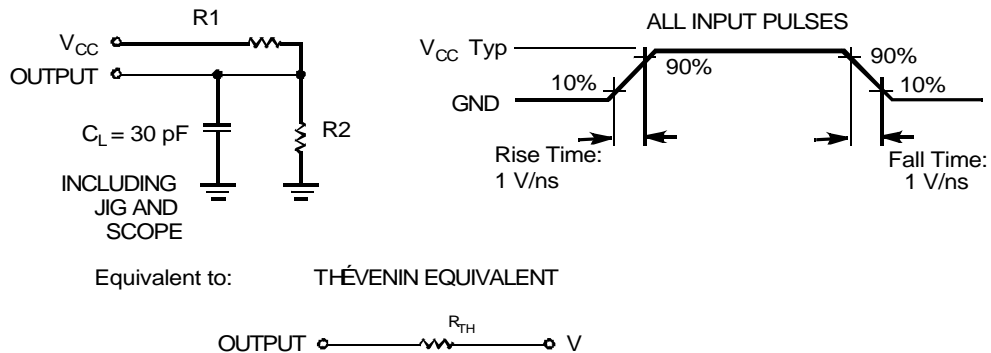
7. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ)}, T_A = 25°C.

8. Tested initially and after any design or process changes that may affect these parameters.

Thermal Resistance

| Parameter | Description | Test Conditions | BGA | Unit |
|---------------|---|--|-----|------|
| θ_{JA} | Thermal Resistance (Junction to Ambient) ^[8] | Still Air, soldered on a 3 x 4.5 inch, two-layer printed circuit board | 55 | C/W |
| θ_{JC} | Thermal Resistance (Junction to Case) ^[8] | | 16 | C/W |

AC Test Loads and Waveforms

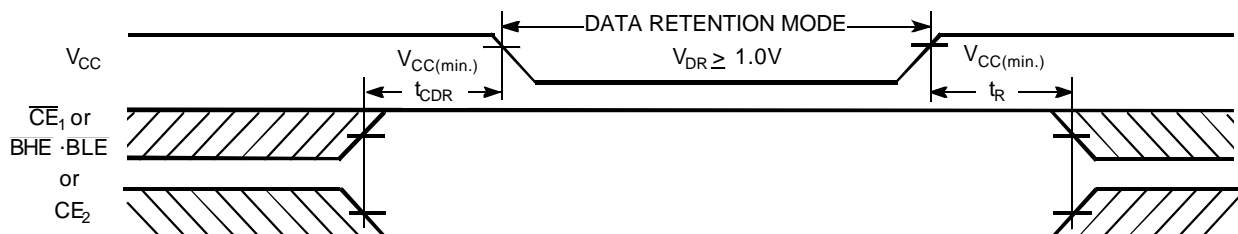


| Parameters | 1.8V | UNIT |
|------------|-------|----------|
| R1 | 13500 | Ω |
| R2 | 10800 | Ω |
| R_{TH} | 6000 | Ω |
| V_{TH} | 0.80 | V |

Data Retention Characteristics

| Parameter | Description | Conditions | Min. | Typ. | Max. | Unit |
|-----------------|--------------------------------------|---|----------|------|------|---------|
| V_{DR} | V_{CC} for Data Retention | | 1.0 | | 2.2 | V |
| I_{CCDR} | Data Retention Current | $V_{CC}=1.0V, CE_1 \geq V_{CC} - 0.2V, CE_2 \leq 0.2V, V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$ | L | | 15 | μA |
| | | | LL | | 10 | |
| $t_{CDR}^{[8]}$ | Chip Deselect to Data Retention Time | | 0 | | | ns |
| $t_R^{[9]}$ | Operation Recovery Time | | t_{RC} | | | ns |

Data Retention Waveform^[10]



Notes:

- Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)} > 100 \mu s$ or stable at $V_{CC(min.)} > 100 \mu s$.
- $\overline{BHE} \cdot \overline{BLE}$ is the AND of both \overline{BHE} and \overline{BLE} . Chip can be deselected by either disabling the chip enable signals or by disabling both \overline{BHE} and \overline{BLE} .

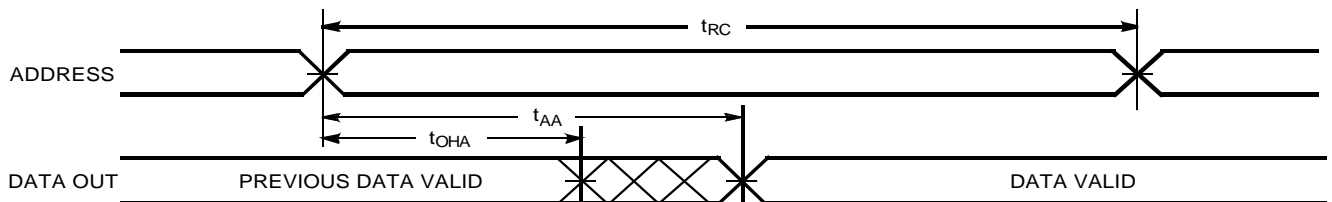


Switching Characteristics (over the operating range)^[11]

| Parameter | Description | CY62167DV20-55 | | CY62167DV20-70 | | Unit |
|-----------------------------------|---|----------------|------|----------------|------|------|
| | | Min. | Max. | Min. | Max. | |
| Read Cycle | | | | | | |
| t _{RC} | Read Cycle Time | 55 | | 70 | | ns |
| t _{AA} | Address to Data Valid | | 55 | | 70 | ns |
| t _{OHA} | Data Hold from Address Change | 10 | | 10 | | ns |
| t _{ACE} | CE ₁ LOW or CE ₂ HIGH to Data Valid | | 55 | | 70 | ns |
| t _{DOE} | OE LOW to Data Valid | | 25 | | 35 | ns |
| t _{LZOE} | OE LOW to Low Z ^[12] | 5 | | 5 | | ns |
| t _{HZOE} | OE HIGH to High Z ^[12, 13] | | 20 | | 25 | ns |
| t _{LZCE} | CE ₁ LOW or CE ₂ HIGH to Low Z ^[12] | 10 | | 10 | | ns |
| t _{HZCE} | CE ₁ HIGH or CE ₂ LOW to High Z ^[12, 13] | | 20 | | 25 | ns |
| t _{PU} | CE ₁ LOW or CE ₂ HIGH to Power-up | 0 | | 0 | | ns |
| t _{PD} | CE ₁ HIGH or CE ₂ LOW to Power-down | | 55 | | 70 | ns |
| t _{DBE} | BLE/BHE LOW to Data Valid | | 55 | | 70 | ns |
| t _{LZBE} ^[10] | BLE/BHE LOW to Low Z ^[12] | 10 | | 5 | | ns |
| t _{HZBE} | BLE/BHE HIGH to High-Z ^[12, 13] | | 20 | | 25 | ns |
| Write Cycle^[14] | | | | | | |
| t _{WC} | Write Cycle Time | 55 | | 70 | | ns |
| t _{SCE} | CE ₁ LOW or CE ₂ HIGH to Write End | 40 | | 60 | | ns |
| t _{AW} | Address Set-up to Write End | 40 | | 60 | | ns |
| t _{HA} | Address Hold from Write End | 0 | | 0 | | ns |
| t _{SA} | Address Set-up to Write Start | 0 | | 0 | | ns |
| t _{PWE} | WE Pulse Width | 40 | | 45 | | ns |
| t _{BW} | BLE/BHE LOW to Write End | 45 | | 60 | | ns |
| t _{SD} | Data Set-up to Write End | 25 | | 30 | | ns |
| t _{HD} | Data Hold from Write End | 0 | | 0 | | ns |
| t _{HZWE} | WE LOW to High Z ^[12, 13] | | 20 | | 25 | ns |
| t _{LZWE} | WE HIGH to Low Z ^[12] | 10 | | 10 | | ns |

Switching Waveforms

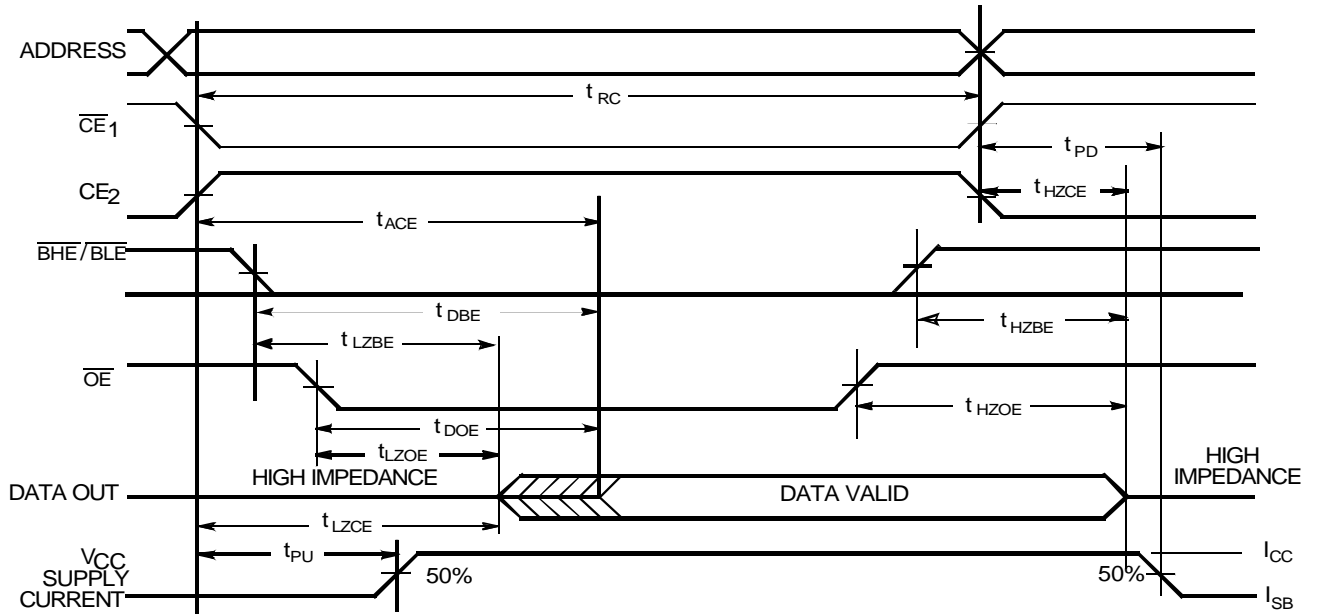
Read Cycle No. 1 (Address Transition Controlled)^[15, 16]



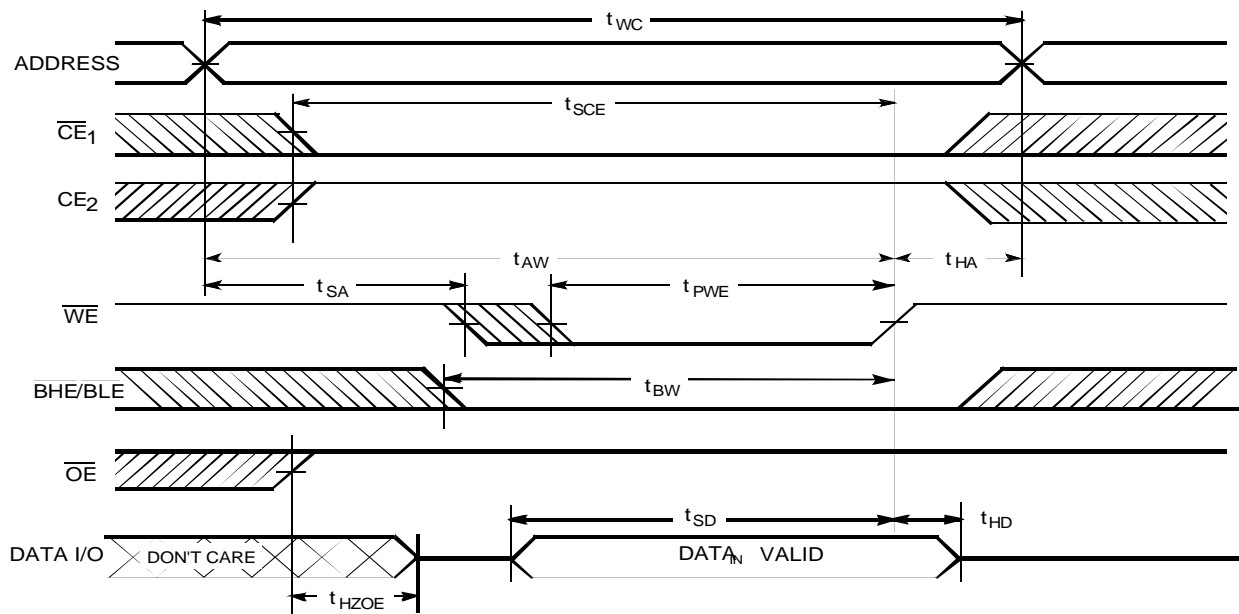
Notes:

11. Test conditions assume signal transition time of 2 ns or less, timing reference levels of V_{CC(typ.)}/2, input pulse levels of 0 to V_{CC(typ.)}, and output loading of the specified I_{OL}.
12. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
13. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.
14. The internal Write time of the memory is defined by the overlap of WE, CE₁ = V_{IL}, BHE and/or BLE = V_{IL}.
15. Device is continuously selected. OE, CE₁ = V_{IL}, CE₂ = V_{IH}
16. WE is HIGH for Read cycle.

Switching Waveforms (continued)
Read Cycle No. 2 (OE Controlled)^[16, 17]



Write Cycle No. 1 (WE Controlled)^[14, 18, 19, 20]

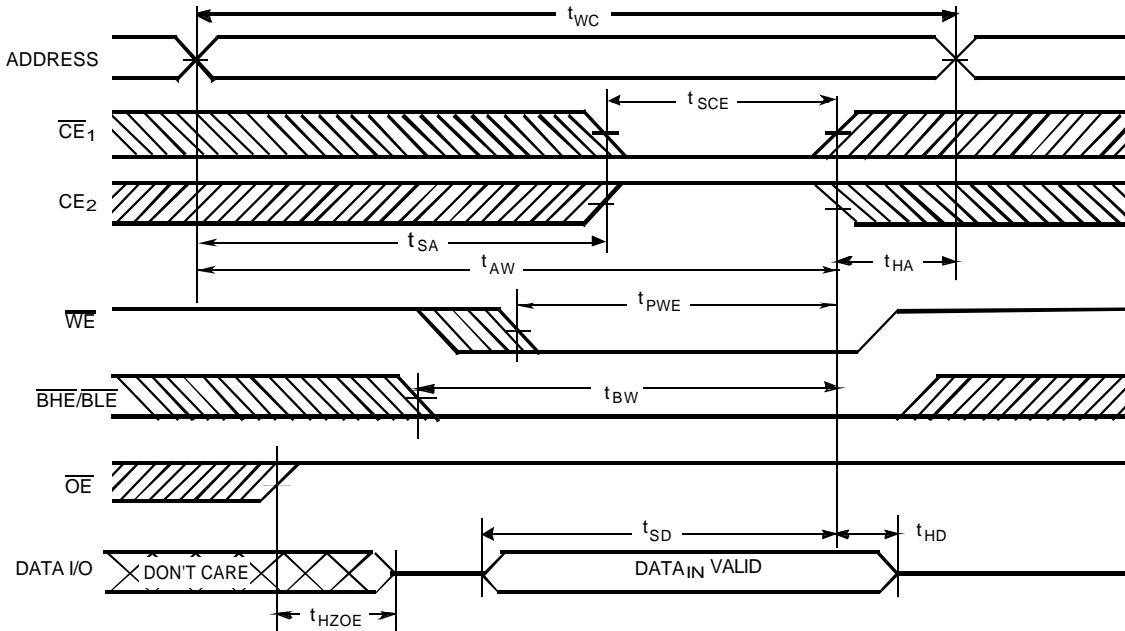


Notes:

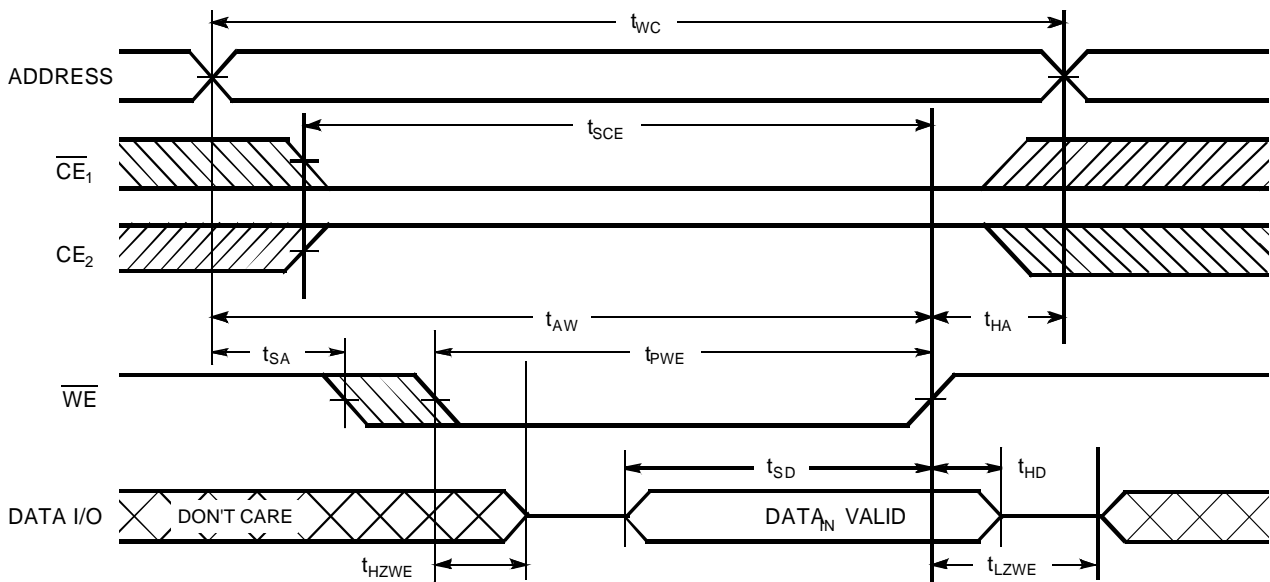
17. Address valid prior to or coincident with \overline{CE}_1 , \overline{BHE} , \overline{BLE} transition LOW and CE_2 transition HIGH.
18. Data I/O is high-impedance if $OE = V_{IH}$.
19. If \overline{CE}_1 goes HIGH or CE_2 goes LOW simultaneously with \overline{WE} HIGH, the output remains in a high-impedance state.
20. During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

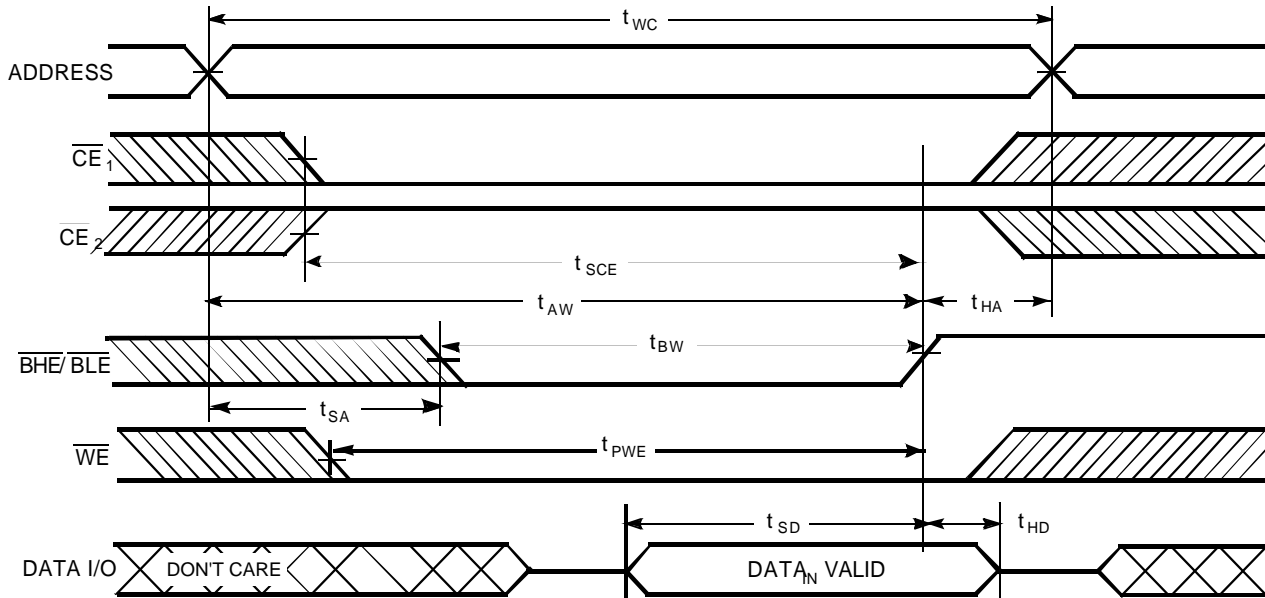
Write Cycle No. 2 (CE1 or CE2 Controlled)^[14, 18, 19, 20]



Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW)^[19, 20]



Switching Waveforms (continued)
Write Cycle No. 4(BHE/BLE Controlled, OE LOW)^[19]



Truth Table

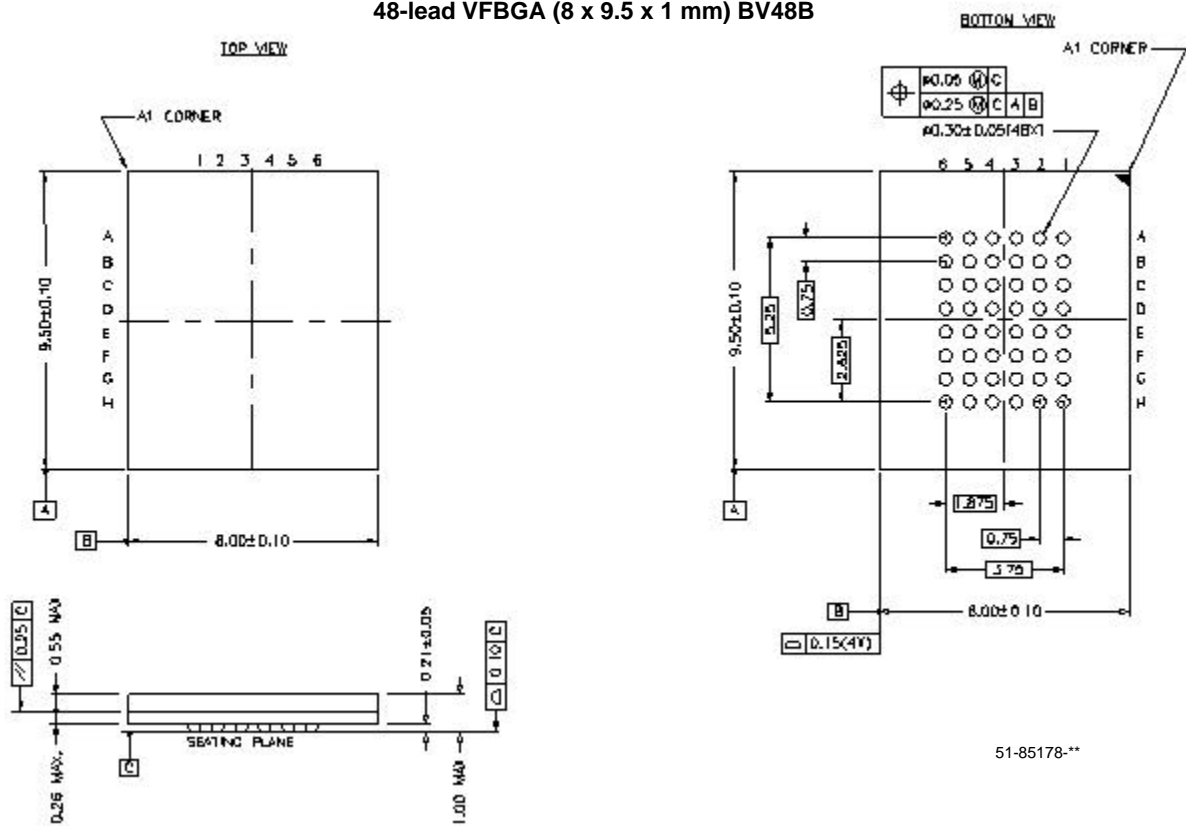
| CE ₁ | CE ₂ | WE | OE | BHE | BLE | Input / Outputs | Mode | Power |
|-----------------|-----------------|----|----|-----|-----|--|---------------------|----------------------------|
| H | X | X | X | X | X | High Z | Deselect/Power-down | Standby (I _{SB}) |
| X | L | X | X | X | X | High Z | Deselect/Power-down | Standby (I _{SB}) |
| X | X | X | X | H | H | High Z | Deselect/Power-down | Standby (I _{SB}) |
| L | H | H | L | L | L | Data Out (I/O0–I/O15) | Read | Active (I _{CC}) |
| L | H | H | L | H | L | Data Out (I/O0–I/O7); High Z (I/O8–I/O15) | Read | Active (I _{CC}) |
| L | H | H | L | L | H | High Z (I/O0–I/O7); Data Out (I/O8–I/O15) | Read | Active (I _{CC}) |
| L | H | H | H | L | H | High Z | Output Disabled | Active (I _{CC}) |
| L | H | H | H | H | L | High Z | Output Disabled | Active (I _{CC}) |
| L | H | H | H | L | L | High Z | Output Disabled | Active (I _{CC}) |
| L | H | L | X | L | L | Data In (I/O0–I/O15) | Write | Active (I _{CC}) |
| L | H | L | X | H | L | Data In (I/O0–I/O7); High Z (I/O8–I/O15) | Write | Active (I _{CC}) |
| L | H | L | X | L | H | High Z (I/O0–I/O7); Data In (I/O8–I/O15) | Write | Active (I _{CC}) |

Ordering Information

| Speed (ns) | Ordering Code | Package Name | Package Type | Operating Range |
|------------|---------------------|--------------|---|-----------------|
| 55 | CY62167DV20L-55BVI | BV48B | 48-ball Fine Pitch BGA (8.0 x 9.5 x 1.0 mm) | Industrial |
| | CY62167DV20LL-55BVI | BV48B | 48-ball Fine Pitch BGA (8.0 x 9.5 x 1.0 mm) | |
| 70 | CY62167DV20L-70BVI | BV48B | 48-ball Fine Pitch BGA (8.0 x 9.5 x 1.0 mm) | Industrial |
| | CY62167DV20LL-70BVI | BV48B | 48-ball Fine Pitch BGA (8.0 x 9.5 x 1.0 mm) | |

Package Diagrams

48-lead VFBGA (8 x 9.5 x 1 mm) BV48B



51-85178-**

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Document History Page

| Document Title: CY62167DV20 MoBL2™ 16-Mb (1024K x 16) Static RAM Document Number: 38-05327 | | | | |
|---|----------------|-------------------|------------------------|--|
| REV. | ECN NO. | Issue Date | Orig. of Change | Description of Change |
| ** | 118407 | 09/30/02 | GUG | New Data Sheet |
| A | 123691 | 02/11/03 | DPM | Changed Advance Information to Preliminary Added package diagram |
| B | 131496 | 11/25/03 | XRJ/LDZ | Changed from Preliminary to Final Added MoBL2™ to title Added package name BV48B |